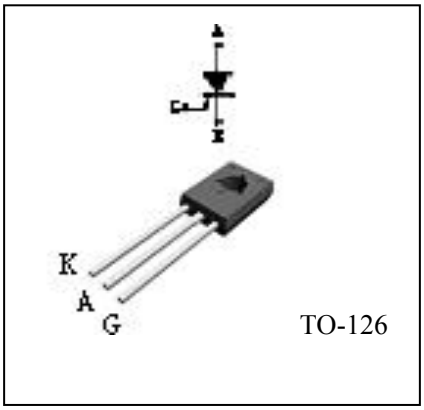
isc Thyristors C106M

FEATURES

- Glassivated surface for reliability and uniformity
- Practical level triggering and holding characteristics
- Designed for high volume consumer applications such as temperature, light, and speed control; process and remote control, and warning systems where reliability of operation Is important.
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	MIN	UNIT
V_{DRM}	Repetitive peak off-state voltage	600	V
V_{RRM}	Repetitive peak off-state voltage	600	V
$I_{T(AV)}$	Average on-state current	2.5	A
$I_{T(RMS)}$	RMS on-state current	4	A
P_{GM}	Peak gate power	0.5	W
$P_{G(AV)}$	Average gate power	0.2	W
I_{TSM}	Non-repetitive peak on-state current	20	A
T_j	Operating junction temperature	110	℃
T_{stg}	Storage temperature	-40~+ 150	℃

ELECTRICAL CHARACTERISTICS (T_C=25℃ unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
I_{RRM}	Repetitive peak reverse current	V_{RRM}=600V V_{RRM}=600V, T_j= 125℃		10 200	μA
I_{DRM}	Repetitive peak off-state current	V_{DRM}=600V V_{DRM}=600V, T_j= 125℃		10 200	μA
I_{GT}	Gate trigger current	V_D= 6V; R_L=100Ω , R_{GK}=1KΩ	10	200	μA
V_{TM}	On-state voltage	I_T= 8A		1.75	V
I_H	Holding current	V_D=24V, R_{GK}=1KΩ , I_{TM}=4A		5	mA
V_{GT}	Gate trigger voltage	V_D= 12V; R_L=100Ω , R_{GK}=1KΩ		0.8	V

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